

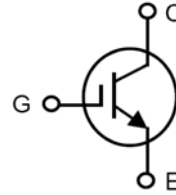
**High Voltage
XPT™ IGBT**
IXYH12N250C

$$V_{CES} = 2500V$$

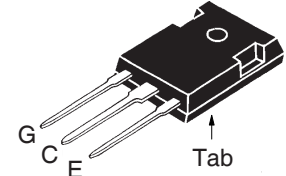
$$I_{C110} = 12A$$

$$V_{CE(sat)} \leq 4.50V$$

$$t_{fi(typ)} = 136ns$$



TO-247 AD


 G = Gate C = Collector
 E = Emitter Tab = Collector

| Symbol | Test Conditions | Maximum Ratings | |
|-------------------------|--|-----------------------|------------|
| V_{CES} | $T_J = 25^\circ C$ to $175^\circ C$ | 2500 | V |
| V_{CGR} | $T_J = 25^\circ C$ to $175^\circ C$, $R_{GE} = 1M\Omega$ | 2500 | V |
| V_{GES} | Continuous | ± 20 | V |
| V_{GEM} | Transient | ± 30 | V |
| I_{C25} | $T_C = 25^\circ C$ | 28 | A |
| I_{C110} | $T_C = 110^\circ C$ | 12 | A |
| I_{CM} | $T_C = 25^\circ C$, 1ms | 80 | A |
| SSOA (RBSOA) | $V_{GE} = 15V$, $T_{VJ} = 150^\circ C$, $R_G = 10\Omega$ Clamped Inductive Load | $I_{CM} = 48$ 1500 | A V |
| P_C | $T_C = 25^\circ C$ | 310 | W |
| T_J | | -55 ... +175 | $^\circ C$ |
| T_{JM} | | 175 | $^\circ C$ |
| T_{stg} | | -55 ... +175 | $^\circ C$ |
| T_L | Maximum Lead Temperature for Soldering | 300 | $^\circ C$ |
| T_{SOLD} | 1.6 mm (0.062in.) from Case for 10s | 260 | $^\circ C$ |
| M_d | Mounting Torque | 1.13/10 | Nm/lb.in. |
| Weight | | 6 | g |

Features

- High Voltage Package
- High Blocking Voltage
- High Peak Current Capability
- Low Saturation Voltage

Advantages

- Low Gate Drive Requirement
- High Power Density

Applications

- Switch-Mode and Resonant-Mode Power Supplies
- Uninterruptible Power Supplies (UPS)
- Laser Generators
- Capacitor Discharge Circuits
- AC Switches

| Symbol | Test Conditions ($T_J = 25^\circ C$, Unless Otherwise Specified) | Characteristic Values | | |
|---------------|---|-----------------------|--------------|--------------------|
| | | Min. | Typ. | Max. |
| BV_{CES} | $I_C = 250\mu A$, $V_{GE} = 0V$ | 2500 | | V |
| $V_{GE(th)}$ | $I_C = 250\mu A$, $V_{CE} = V_{GE}$ | 3.0 | | 5.0 V |
| I_{CES} | $V_{CE} = V_{CES}$, $V_{GE} = 0V$ $T_J = 150^\circ C$ | | | 10 μA 3 mA |
| I_{GES} | $V_{CE} = 0V$, $V_{GE} = \pm 20V$ | | | ± 100 nA |
| $V_{CE(sat)}$ | $I_C = 12A$, $V_{GE} = 15V$, Note 1 $T_J = 150^\circ C$ | | 3.70 5.55 | V V |

| Symbol Test Conditions ($T_J = 25^\circ\text{C}$ Unless Otherwise Specified) | | Characteristic Values | | |
|--|--|-----------------------|------|--------------------|
| | | Min. | Typ. | Max. |
| g_{fs} | $I_C = 12\text{A}, V_{CE} = 10\text{V}$, Note 1 | 7 | 12 | S |
| R_{Gi} | Gate Input Resistance | | 6.9 | Ω |
| C_{ies} | $V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$ | | 1370 | pF |
| C_{oes} | | | 46 | pF |
| C_{res} | | | 16 | pF |
| $Q_{g(on)}$ | $I_C = 12\text{A}, V_{GE} = 15\text{V}, V_{CE} = 0.5 \cdot V_{CES}$ | | 56 | nC |
| Q_{ge} | | | 6 | nC |
| Q_{gc} | | | 28 | nC |
| $t_{d(on)}$ | Inductive load, $T_J = 25^\circ\text{C}$ $I_C = 12\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 10\Omega$ Note 2 | | 12 | ns |
| t_{ri} | | | 16 | ns |
| E_{on} | | | 3.56 | mJ |
| $t_{d(off)}$ | | | 167 | ns |
| t_{fi} | | | 136 | ns |
| E_{off} | | | 1.70 | mJ |
| $t_{d(on)}$ | Inductive load, $T_J = 150^\circ\text{C}$ $I_C = 12\text{A}, V_{GE} = 15\text{V}$ $V_{CE} = 0.5 \cdot V_{CES}, R_G = 10\Omega$ Note 2 | | 12 | ns |
| t_{ri} | | | 20 | ns |
| E_{on} | | | 4.78 | mJ |
| $t_{d(off)}$ | | | 195 | ns |
| t_{fi} | | | 138 | ns |
| E_{off} | | | 1.95 | mJ |
| R_{thJC} | | | 0.48 | $^\circ\text{C/W}$ |
| R_{thCS} | | 0.21 | | $^\circ\text{C/W}$ |



Notes:

1. Pulse test, $t \leq 300\mu\text{s}$, duty cycle, $d \leq 2\%$.
2. Switching times & energy losses may increase for higher V_{CE} (clamp), T_J or R_G .

ADVANCE TECHNICAL INFORMATION

The product presented herein is under development. The Technical Specifications offered are derived from a subjective evaluation of the design, based upon prior knowledge and experience, and constitute a "considered reflection" of the anticipated result. IXYS reserves the right to change limits, test conditions, and dimensions without notice.

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| | | | | | | | | | | |
|--|-----------|-----------|-----------|-----------|--------------|--------------|--------------|--------------|--------------|-------------|
| IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents: | 4,835,592 | 4,931,844 | 5,049,961 | 5,237,481 | 6,162,665 | 6,404,065 B1 | 6,683,344 | 6,727,585 | 7,005,734 B2 | 7,157,338B2 |
| | 4,860,072 | 5,017,508 | 5,063,307 | 5,381,025 | 6,259,123 B1 | 6,534,343 | 6,710,405 B2 | 6,759,692 | 7,063,975 B2 | |
| | 4,881,106 | 5,034,796 | 5,187,117 | 5,486,715 | 6,306,728 B1 | 6,583,505 | 6,710,463 | 6,771,478 B2 | 7,071,537 | |

Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

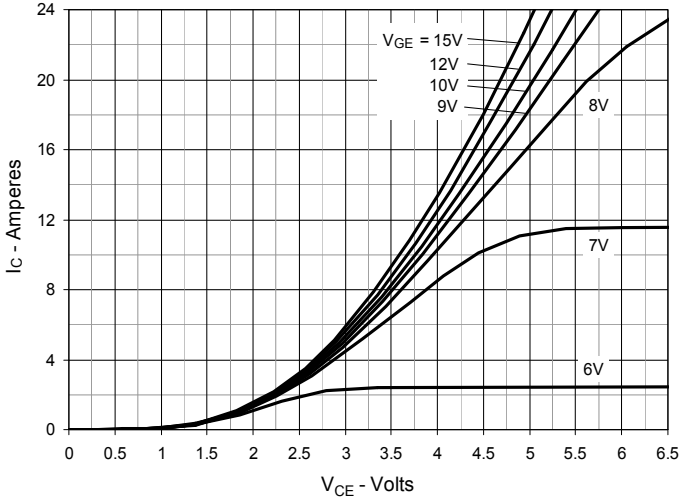


Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

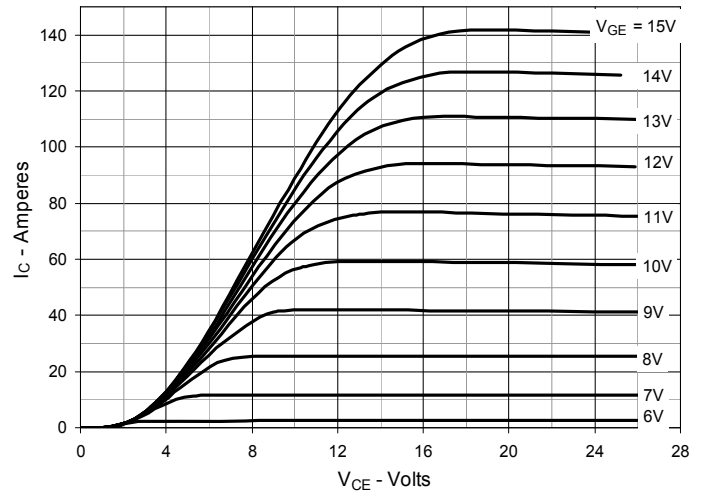


Fig. 3. Output Characteristics @ $T_J = 150^\circ\text{C}$

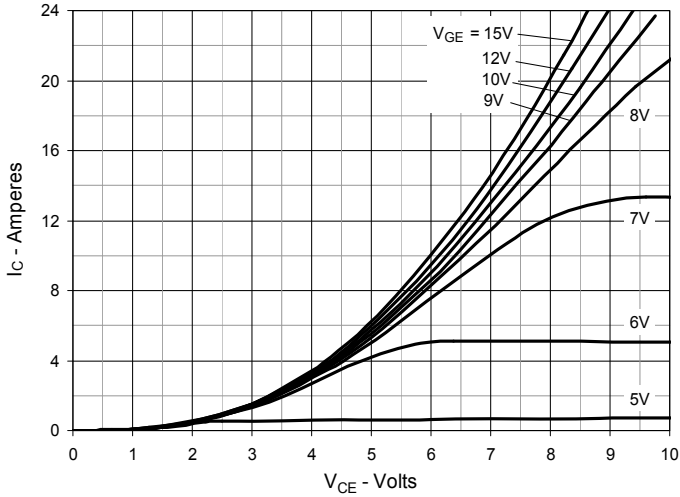


Fig. 4. Dependence of $V_{CE(sat)}$ on Junction Temperature

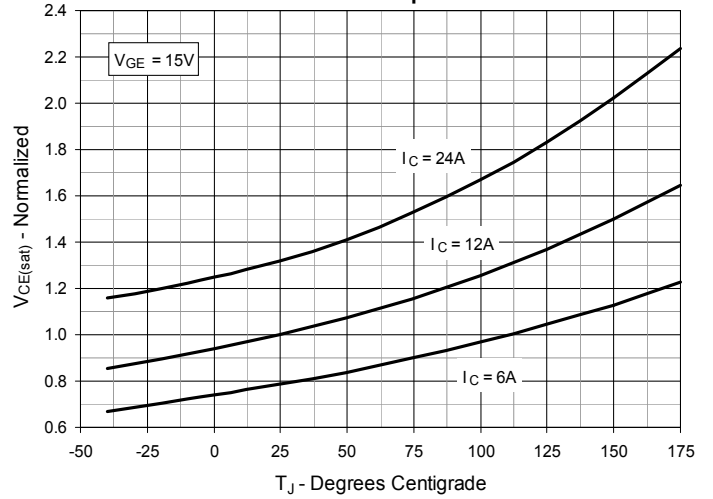


Fig. 5. Collector-to-Emitter Voltage vs. Gate-to-Emitter Voltage

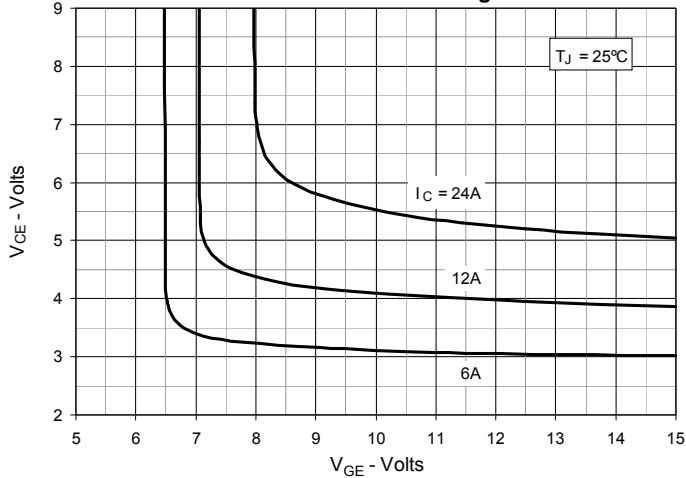


Fig. 6. Input Admittance

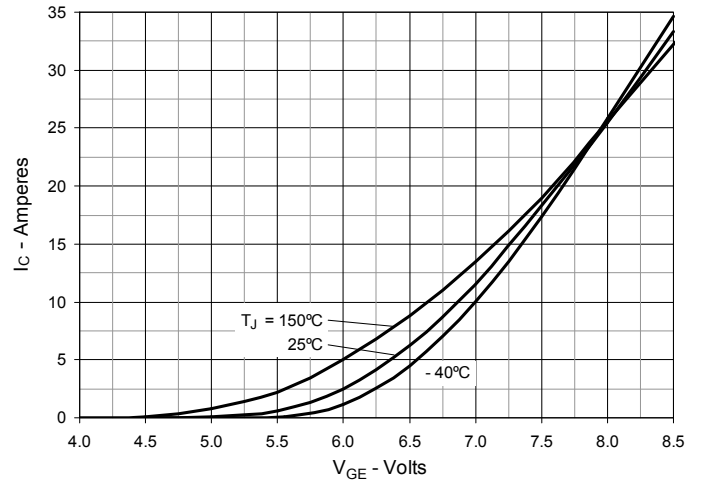


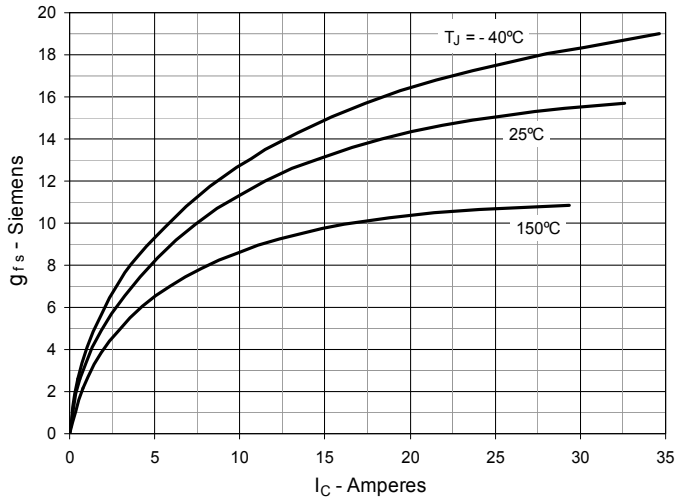
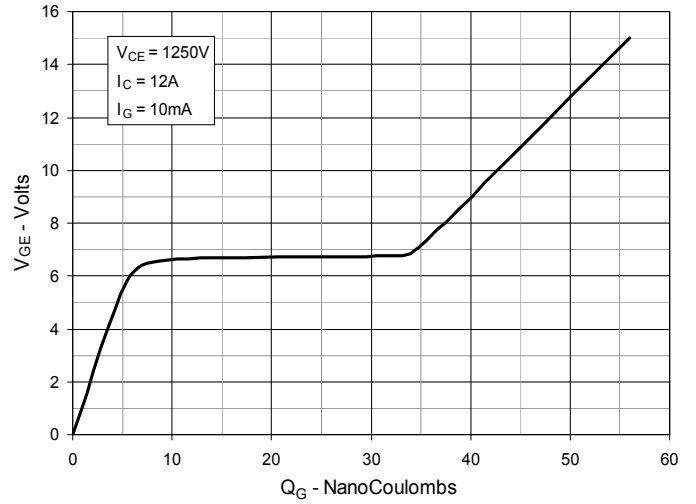
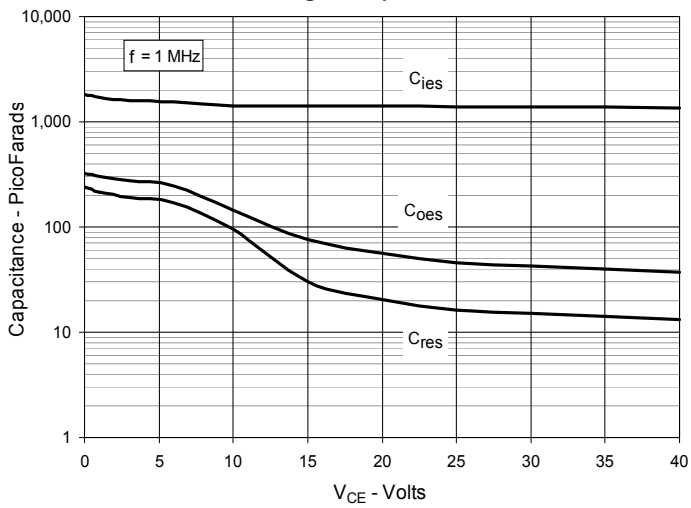
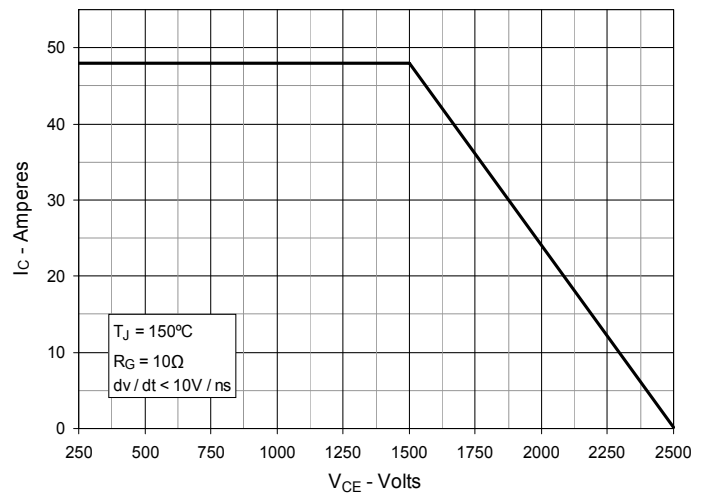
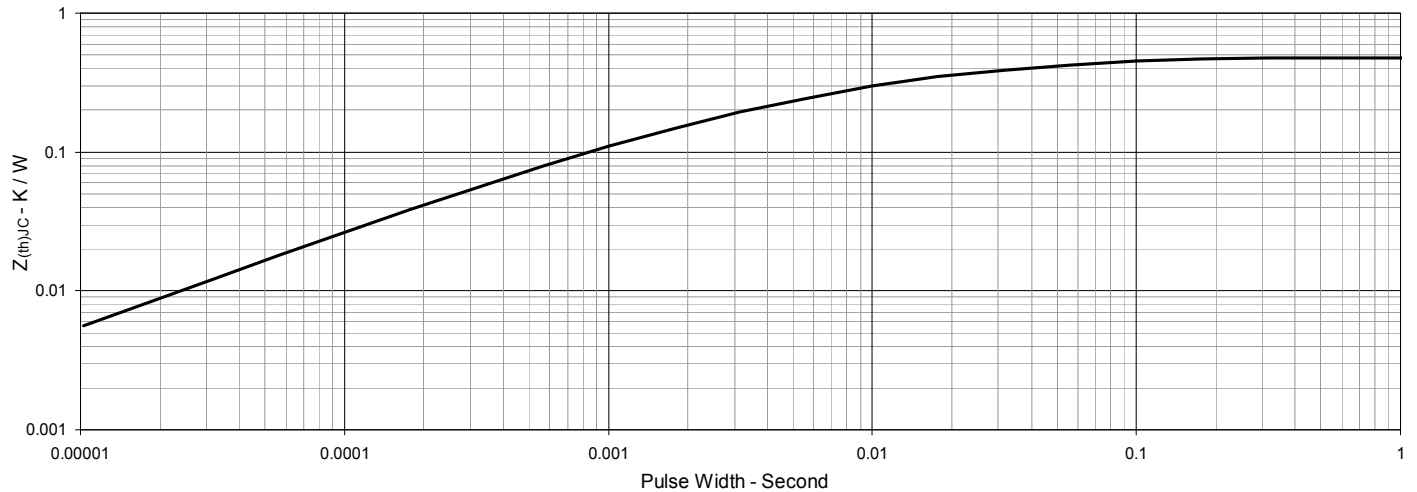
Fig. 7. Transconductance

Fig. 8. Gate Charge

Fig. 9. Capacitance

Fig. 10. Reverse-Bias Safe Operating Area

Fig. 11. Maximum Transient Thermal Impedance


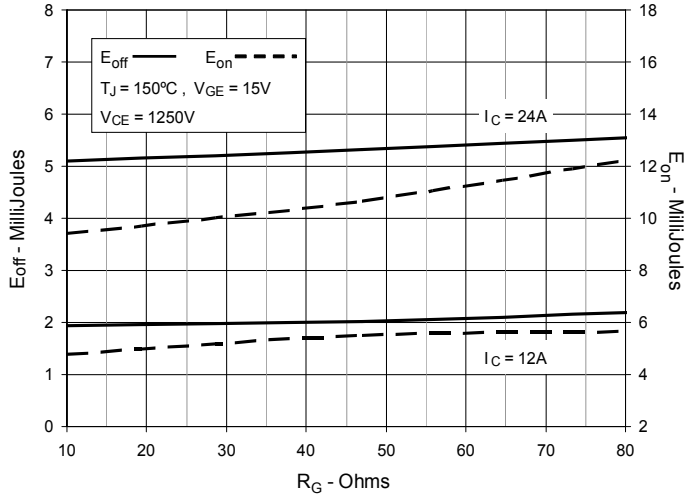
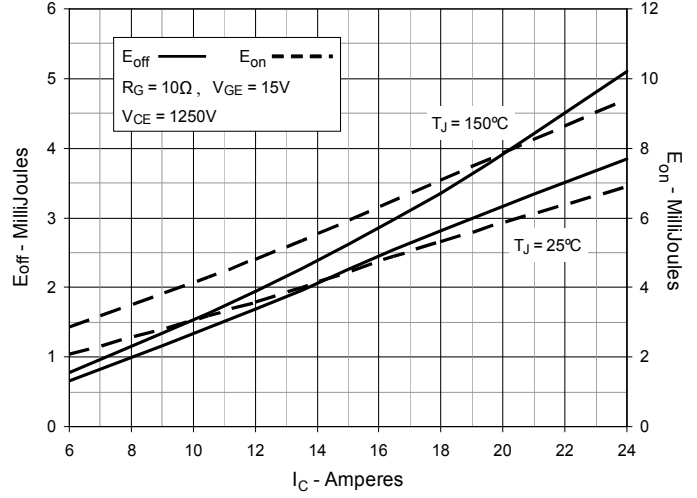
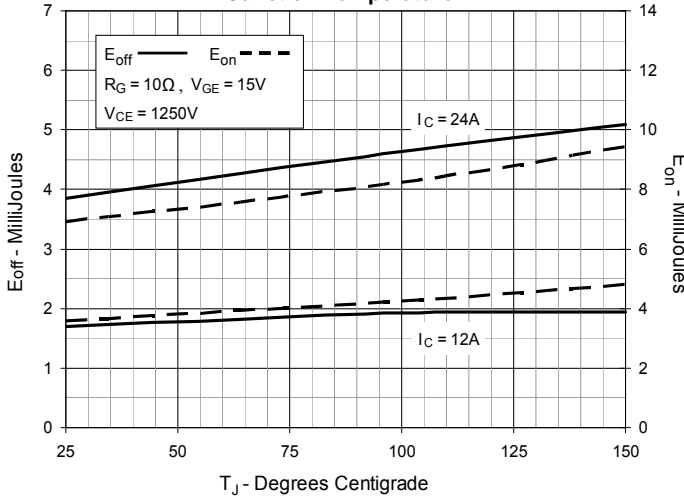
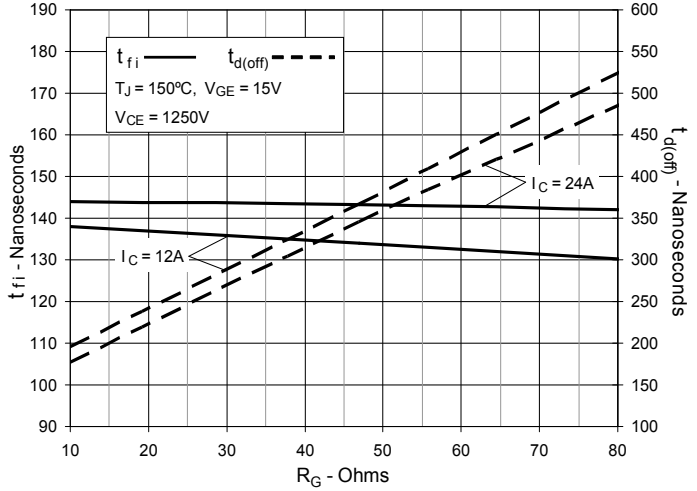
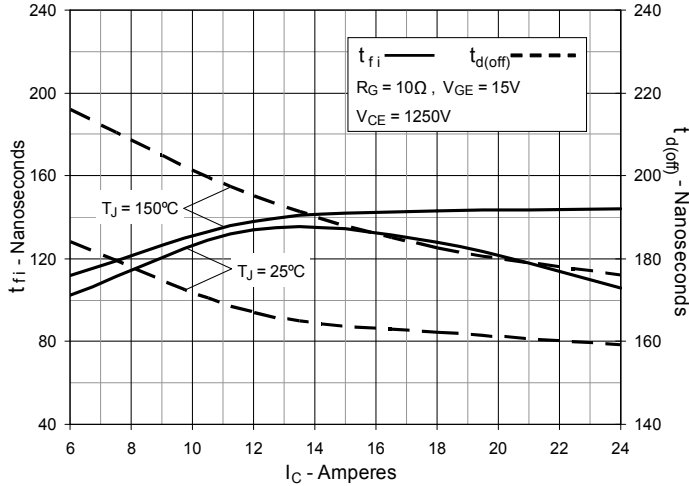
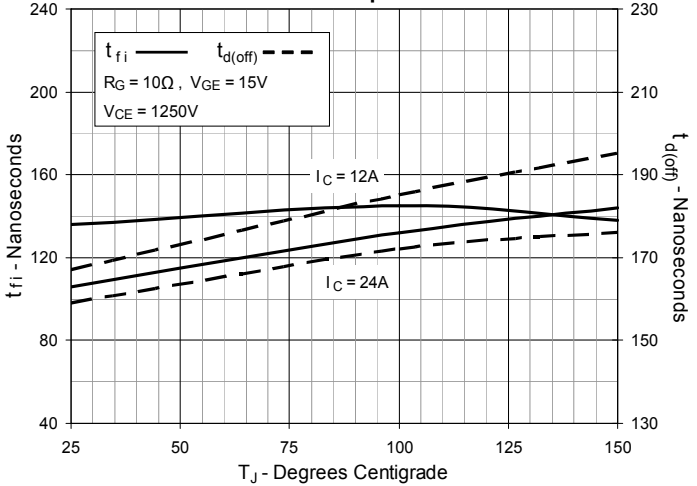
Fig. 12. Inductive Switching Energy Loss vs. Gate Resistance

Fig. 13. Inductive Switching Energy Loss vs. Collector Current

Fig. 14. Inductive Switching Energy Loss vs. Junction Temperature

Fig. 15. Inductive Turn-off Switching Times vs. Gate Resistance

Fig. 16. Inductive Turn-off Switching Times vs. Collector Current

Fig. 17. Inductive Turn-off Switching Times vs. Junction Temperature


Fig. 18. Inductive Turn-on Switching Times vs. Gate Resistance

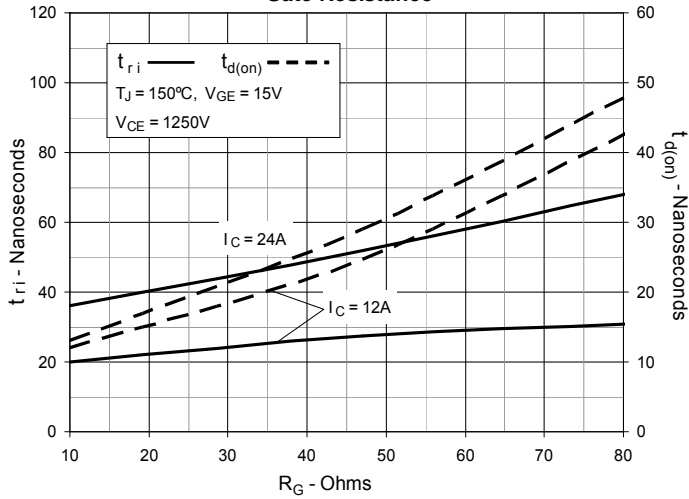


Fig. 19. Inductive Turn-on Switching Times vs. Collector Current

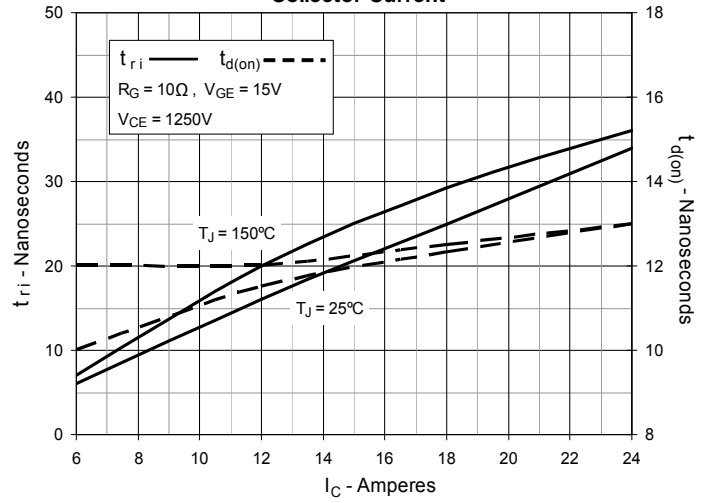


Fig. 20. Inductive Turn-on Switching Times vs. Junction Temperature

